

Industrial SD Card

3SE3

Customer: _____

Customer

Part

Number: _____

Innodisk

Part

Number: _____

Innodisk

Model Name: _____

Date: _____

Innodisk Approver	Customer Approver

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5. PART NUMBER RULE 15

REVISION HISTORY

Revision	Description	Date
Preliminary	First release	JAN, 2019
Preliminary v2	Modified typo, removed decimal points in performance chart Update Appendix documents.	JAN 23 rd , 2019
Rev. 1.0	Add LBA of 4GB and 8GB	June, 2019
Rev. 1.1	Update user capacity	July, 2019
Rev 1.2	Modify TBW	July, 2019

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1. Product Overview

1.1 Introduction of Innodisk Industrial MicroSD 3SE3

Innodisk 3SE3 is an industrial-grade MicroSD card solution with an integrated industrial controller, which is designed for embedded applications. With enhanced flash technologies and a powerful configurable BCH ECC engine, SD 3SE3 can achieve high-speed data transfer rates.

Innodisk Industrial MicroSD 3SE3 provides a wide range of capacities from 4GB to 8GB with SLC NAND Flash, and is fully compliant with SD3.0 and SD2.0 specifications.

Innodisk Industrial MicroSD 3SE3 are specifically designed for industrial PC and embedded applications for high performance. With its low power consumption and the above mentioned features, Innodisk Industrial MicroSD 3SE3 can be applied for industrial automation, SBC (single-board computer), medical equipment, infotainment, and mobile applications.

1.2 Product View and Models

Innodisk Industrial MicroSD 3SE3 is available from 4GB up to 8GB capacities within SLC Flash IC.



Figure 1: Innodisk Industrial MicroSD 3SE3

1.3 SD 3.0 Interface

Innodisk Industrial MicroSD 3SE3 support SD 3.0 interface, and backward compliant to SD 2.0 interface.

2. Product Specifications

2.1 Capacity and Device Parameters

Innodisk Industrial MicroSD card device parameters are shown in Table 1.

Table 1: Device parameters

Capacity	LBA	User Capacity(MB)
4GB	7929856	3,872
8GB	15859712	7,744

2.2 Performance

Burst Transfer Rate: up to 104 MB/s in SD 3.0 SDR104

Table 2: Performance

Capacity	4GB	8GB
Class	10	10
Sequential Read (max.)	30 MB/sec	29 MB/sec
Sequential Write (max.)	23 MB/sec	23 MB/sec

Note: Base on CrystalDiskMark 5.1.2 with file size 1000MB

2.3 Electrical Specifications

2.3.1 Power Requirement

Table 3: Innodisk Industrial MicroSD card Power Requirement

Item	Symbol	Rating	Unit
Input voltage	V _{IN}	2.7V~3.6V	V

2.3.2 Power Consumption

Table 4: Power Consumption

Mode	Power Consumption (mA)
Read	95.5 (max.)
Write	111.3 (max.)
Idle	0.1 (max.)

* Target: Industrial MicroSD 3SE3 SLC 8GB

2.4 Environmental Specifications

2.4.1 Temperature Ranges

Table 5: Temperature range for MicroSD card 3SE3

Temperature	Range
Operating	Extended Grade: -25°C to +85°C
	Industrial Grade: -40°C to +85°C
Storage	-55°C to +95°C

2.4.2 Humidity

Relative Humidity: 10-95%, non-condensing

2.4.3 Shock and Vibration

Table 6: Shock/Vibration Testing for Industrial MicroSD card

Reliability	Test Conditions	Reference Standards
Vibration	7 Hz to 2K Hz, 20G, 3 axes	IEC 68-2-6
Mechanical Shock	Duration: 0.5ms, 1500 G, 3 axes	IEC 68-2-27

2.4.4 Mean Time between Failures (MTBF)

Table 7 summarizes the MTBF prediction results for various Industrial MicroSD card configurations. The analysis was performed using a RAM Commander™ failure rate prediction.

- **Failure Rate:** The total number of failures within an item population, divided by the total number of life units expended by that population, during a particular measurement interval under stated condition.
- **Mean Time between Failures (MTBF):** A basic measure of reliability for repairable items: The mean number of life units during which all parts of the item perform within their specified limits, during a particular measurement interval under stated conditions.

Table 7: Industrial MicroSD card MTBF

Product	Condition	MTBF (Hours)
Innodisk Industrial MicroSD 3SE3	Telcordia SR-332 GB, 25°C	>3,000,000

2.5 CE and FCC Compatibility

Industrial MicroSD card conforms to CE and FCC requirements.

2.6 RoHS Compliance

Industrial MicroSD card is fully compliant with RoHS directive.

2.7 Reliability

Parameter	Value
Read Cycles	Unlimited Read Cycles
Wear-Leveling Algorithm	Support
Bad Blocks Management	Support

Error Correct Code	Support
TBW(Sequential Write)	SLC
4GB	213
8GB	426

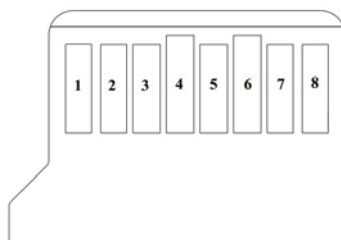
2.8 Transfer Mode

Industrial MicroSD 3SE3 support following transfer mode:

SD 3.0 / SD 2.0

2.9 Pin Assignment

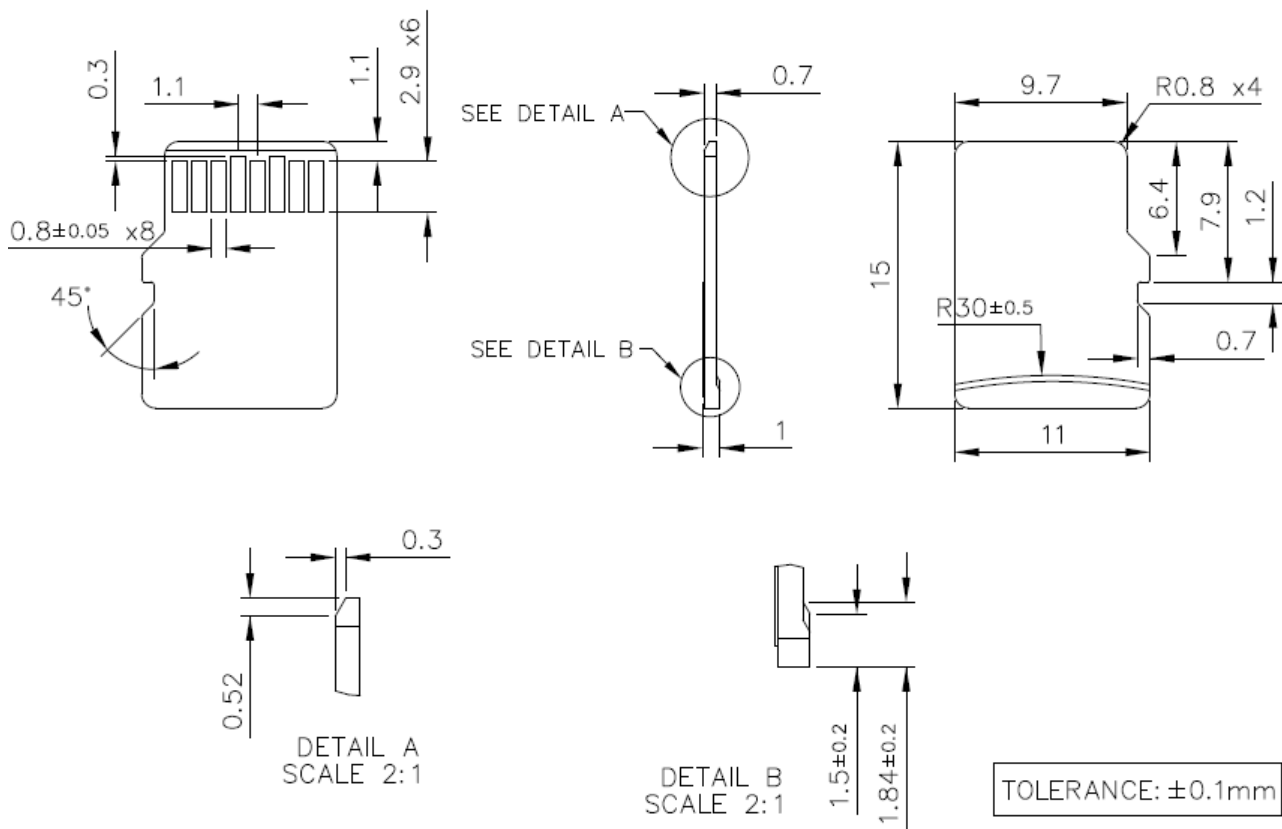
Innodisk Industrial MicroSD 3SE3 compliant with Standard SD SPEC., please refer to Table 8 for pin assignment.



Pin #	Name	Type	Description
1	DAT2 ^{2,5}	I/O	Data Line [Bit 2]
2	CD/DAT3	I/O ³	Card Detect/Data Line[Bit 3]
3	CMD	I/O	Command/Response
4	V _{DD}	S	S Supply Voltage
5	CLK	I	Clock
6	V _{SS}	S	S Supply Voltage GND
7	DAT0	I/O	Data Line [Bit 0]
8	DAT1 ^{2,4}	I/O	Data Line [Bit 1]

Table 8: Innodisk Industrial MicroSD 3SE3 Pin Assignment

2.10 Mechanical Dimensions



2.11 Assembly Weight

An Innodisk Industrial MicroSD card 3.0 within SLC flash ICs, 8GB's weight is 0.25 grams approx.

2.12 Seek Time

Innodisk Industrial MicroSD card is not a magnetic rotating design. There is no seek or rotational latency required.

2.13 Hot Plug

The MicroSD card support hot plug function and can be removed or plugged-in during operation.

2.14 NAND Flash Memory

Innodisk Industrial MicroSD 3SE3 uses Single Level Cell (SLC) NAND flash memory, which is non-volatility, high reliability and high speed memory storage.

3. Theory of Operation

3.1 Overview

Figure 2 shows the operation of Innodisk Industrial MicroSD 3SE3 from the system level, including the major hardware blocks.

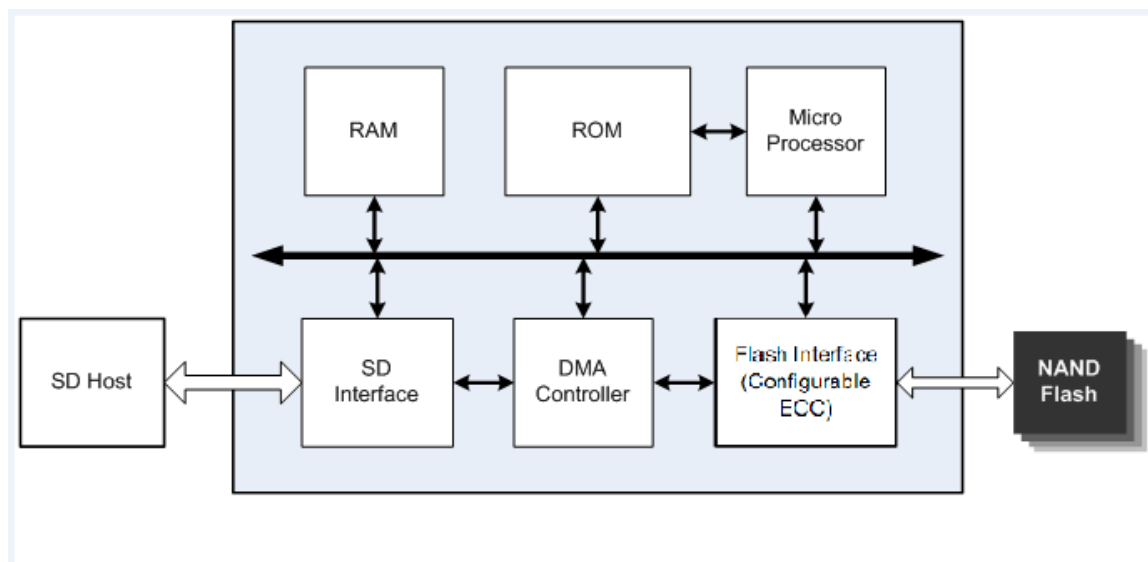


Figure 2: Innodisk Industrial MicroSD 3SE3 Block Diagram

Innodisk Industrial MicroSD 3SE3 integrates a SD 3.0 controller and NAND flash memories. Communication with the host occurs through the host interface, using the standard SD interface.

3.2 SD 3.0 Controller

Innodisk Industrial MicroSD 3SE3 is designed with a SD 3.0 controller, which has single channel for flash interface.

3.3 Error Detection and Correction

Highly sophisticated Error Correction Code algorithms are implemented. The ECC unit consists of the Parity Unit (parity-byte generation) and the Syndrome Unit (syndrome-byte computation). This unit implements an algorithm that can correct from 24 up to 72 bits per 1024 bytes in an ECC block. Code-byte generation during write operations, as well as error detection during read operation, is implemented on the fly without any speed penalties.

3.4 Wear-Leveling

Flash memory can be erased within a limited number of times. This number is called the **erase cycle limit** or **write endurance limit** and is defined by the flash array vendor. The erase cycle limit applies to each individual erase block in the flash device.

Innodisk Industrial MicroSD 3SE3 uses a global wear-leveling algorithm to ensure that consecutive writes of a specific sector are not written physically to the same page/block in the flash. This spreads flash media usage evenly across all pages, thereby extending flash lifetime.

3.5 Bad Blocks Management

Bad Blocks are blocks that contain one or more invalid bits whose reliability are not guaranteed. The Bad Blocks may be presented while the product is shipped, or may develop during the life time of the MicroSD card. When the Bad Blocks is detected, it will be flagged, and not be used anymore. The MicroSD card implement Bad Blocks management, Bad Blocks replacement, Error Correct Code to avoid data error occurred. The functions will be enabled automatically to transfer data from Bad Blocks to spare blocks, and correct error bit.

3.6 Garbage Collection

Garbage collection is used to maintain data consistency and perform continual data cleansing on MicroSD card. It runs as a background process, freeing up valuable controller resources while sorting good data into available blocks, and deleting bad blocks. It also significantly reduces write operations to the drive, thereby increasing the SD's speed and lifespan.

3.7 Power cycling

Innodisk's SD/MSDs provide the complete data protection mechanism during every abnormal power shutdown situation. Such as: power failure at programming data, updating system tables, erasing blocks, etc. The mechanism can maintain the data correctness and increase the reliability of the data stored in the NAND Flash memory.

4. Installation Requirements

4.1 Industrial MicroSD card Pin Directions

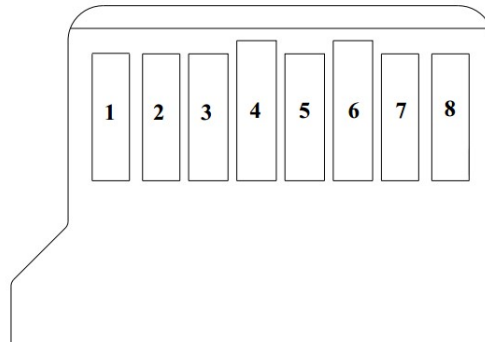


Figure 3: Signal Segment and Power Segment

4.2 Device Driver

No additional device drivers are required.

5. Part Number Rule

CODE	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20
	D	E	S	D	M	-	0	8	G	S	0	2	A	E	1	S	T	-	X	X
Description	Disk	Industrial MicroSD card					Capacity			Category			Flash Mode	Operation Temp.	Internal Control	CH.	Flash	-	Customized Code	
Definition																				
Code 1 st (Disk)													Code 14 th (Operation Temperature)							
D : Disk													E: Extended Grade (-25℃ ~ +85℃)							
Code 2 nd (Feature set)													W: Industrial Grade (-40℃ ~ +85℃)							
E : Embeded Product line													Code 15 th (Internal control)							
Code 3 rd ~5 th (Form factor)													1~9: Substrate Version							
SDM: MicroSD													Code 16 th (Channel of data transfer)							
Code 7 th ~9 th (Capacity)													S: Single Channel							
04G: 4GB													Code 17 th (Flash Type)							
08G: 8GB													T: Micron SLC							
Code 10 th ~12 th (Series)													Code 19 th ~20 th (Customized Code)							
S02: SMI 2702BAC																				
Code 13 th (Flash Mode)																				
A: Async Flash																				

宜鼎國際股份有限公司 Innodisk Corporation

Tel:(02)7703-3000 Fax:(02) 7703-3555 Internet: <http://www.innodisk.com/>

RoHS 自我宣告書 (RoHS Declaration of Conformity)

Manufacturer Product: All Innodisk EM Flash and Dram products

- 一、 宜鼎國際股份有限公司（以下稱本公司）特此保證售予貴公司之所有產品，皆符合歐盟 2011/65/EU 及 (EU) 2015/863 關於 RoHS 之規範要求。

Innodisk Corporation declares that all products sold to the company, are complied with European Union RoHS Directive (2011/65/EU) and (EU) 2015/863 requirement.

- 二、 本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。

Innodisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.

Name of hazardous substance	Limited of RoHS ppm (mg/kg)
鉛 (Pb)	< 1000 ppm
汞 (Hg)	< 1000 ppm
鎘 (Cd)	< 100 ppm
六價鉻 (Cr 6+)	< 1000 ppm
多溴聯苯 (PBBs)	< 1000 ppm
多溴二苯醚 (PBDEs)	< 1000 ppm
鄰苯二甲酸二(2-乙基己基)酯 (DEHP)	< 1000 ppm
鄰苯二甲酸丁酯苯甲酯 (BBP)	< 1000 ppm
鄰苯二甲酸二丁酯 (DBP)	< 1000 ppm
鄰苯二甲酸二異丁酯 (DIBP)	< 1000 ppm

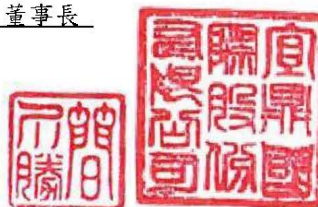
立 保 證 書 人 (Guarantor)

Company name 公司名稱： Innodisk Corporation 宜鼎國際股份有限公司

Company Representative 公司代表人： Randy Chien 簡川勝

Company Representative Title 公司代表人職稱： Chairman 董事長

Date 日期： 2018 / 07 / 01



宜鼎國際股份有限公司 Innodisk Corporation

Tel:(02)7703-3000 Fax:(02) 7703-3555 Internet: <http://www.innodisk.com/>

REACH Declaration of Conformity

Manufacturer Product: All Innodisk EM Flash and Dram products

1. 宜鼎國際股份有限公司（以下稱本公司）特此保證此售予貴公司之產品，皆符合歐盟化學品法案(Registration, Evaluation and Authorization of Chemicals; REACH)之規定
(<http://www.echa.europa.eu/de/candidate-list-table> last updated: 15/01/2018)。所提供之產品包含：(1) 產品或產品所使用到的所有原物料；(2) 包裝材料；(3) 設計、生產及重工過程中所使用到的所有原物料。

We Innodisk Corporation hereby declare that our products are in compliance with the requirements according to the REACH Regulation

(<http://www.echa.europa.eu/de/candidate-list-table> last updated: 15/01/2018).

Products include: 1) Product and raw material used by the product; 2) Packaging material; 3) Raw material used in the process of design, production and rework

2. 本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。

InnoDisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.

立 保 證 書 人 (Guarantor)

Company name 公司名稱：InnoDisk Corporation 宜鼎國際股份有限公司

Company Representative 公司代表人：Randy Chien 簡川勝

Company Representative Title 公司代表人職稱：Chairman 董事長

Date 日期：2018/02/08



MSL Declaration of Conformity

1. Purpose: MSL (Moisture Sensitivity Levels) specification statement for all Innodisk products

2. Scope: For All Innodisk finish goods

3. Responsibilities: QA

4. Reference:

4.1 JEDEC, S-STD-020

4.2 JEDEC, J-STD-033

5. Description

5.1 Innodisk Products Level: All Innodisk products meet MSL Level 1

5.2 Floor Life Time: Refer following table

		Soak Requirements				
	Floor Life	Standard		Accelerated		
Level	Time	Cond degC/%RH	Time (hrs)	Cond degC/%RH	Time (hrs)	Cond degC/%RH
1	unlimited	<=30/85%	168+5/-0	85/85	n/a	n/a
2	1 year	<=30/60%	168+5/-0	85/60	n/a	n/a
2a	4 weeks	<=30/60%	696+5/-0	30/60	120+1/-0	60/60
3	168 hours	<=30/60%	192+5/-0	30/60	40+1/-0	60/60
4	72 hours	<=30/60%	96+2/-0	30/60	20+0.5/-0	60/60
5	48 hours	<=30/60%	72+2/-0	30/60	15+0.5/-0	60/60
5a	24 hours	<=30/60%	48+2/-0	30/60	10+0.5/-0	60/60
6	TOL	<=30/60%	TOL	30/60	n/a	60/60

Innodisk Corporation
Quality Assurance Div
Manager
Yi Chuan Chen
Date: 2018.09.21



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DECLARATION OF CONFORMITY

This Declaration of Conformity is hereby issued to the below named company and for below described device, based on

**Technical Standard: FCC 47 CFR Part 15
Subpart B, Class B
ISED ICES-003 Issue 6, 2016**

General Information

Applicant: Innodisk Corporation
5F., No. 237, Sec. 1, Datong Rd., Xizhi Dist.,
New Taipei City 22161, Taiwan (R.O.C)

Product Description

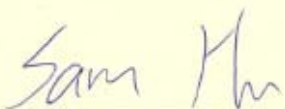
EUT Description: SD 3.0
Brand Name: Innodisk
Model Number: SD 3S*#
\$:Flash type: (S:SLC, I:SLC, M:MLC, T:3D TLC, A~Z:Others);
*:Product line: (E:Embedded, G:EverGreen, R:InnoRobust, S:Server, V:InnoREC, A~Z:Others);
#:Product Generation: (empty, 0~9);
SD type include (Industrial SD Card SD 3.0)

Measurement Facilities

Xindian Lab.: Compliance Certification Services Inc.
No.163-1, Jhongsheng Rd., Xindian Dist., New Taipei City, 23151 Taiwan.
Tel: +886-2-22170894 / Fax: +886-2-22171029

This device has been tested and found to be in compliance with the measurement procedures specified in the Standards & Specifications listed above and as indicated in the measurement report with the number: T170707D04-D

The test results shown in this report are applicable only to the investigated sample identified in this report.



Sam Hu / Assistant Manager

Date: July 12, 2017



VERIFICATION OF COMPLIANCE

This Verification of Compliance is hereby issued to the below named company and for below described product, based on

**Technical Standard: EMC DIRECTIVE 2014/30/EU
(EN55032 / EN55024)**

General Information

Applicant: Innodisk Corporation
5F., No. 237, Sec. 1, Datong Rd., Xizhi Dist.,
New Taipei City 22161, Taiwan (R.O.C)

Product Description

EUT Description: SD 3.0
Brand Name: Innodisk
Model Number: SD 3\$*#
\$:Flash type: (S:SLC, I:iSLC, M:MLC, T:3D TLC, A~Z:Others);
*:Product line: (E:Embedded, G:EverGreen, R:InnoRobust, S:Server, V:InnoREC, A~Z:Others);
#:Product Generation: (empty, 0~9);
SD type include (Industrial SD Card SD 3.0)

Measurement Standard

EN 55032: 2015 / AC: 2016
CISPR 32: 2015 (Ed 2.0) / C1: 2016
EN 61000-3-2: 2014
EN 61000-3-3: 2013
EN 55024: 2010 + A1: 2015
(IEC 61000-4-2: 2008; IEC 61000-4-3: 2006 + A1: 2007 + A2: 2010; IEC 61000-4-4: 2012;
IEC 61000-4-5: 2014; IEC 61000-4-6: 2013; IEC 61000-4-8: 2009; IEC 61000-4-11: 2004)

Measurement Facilities

Xindian Lab.: Compliance Certification Services Inc.
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Tel: +886-2-22170894 / Fax: +886-2-22171029

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Sam Hu / Assistant Manager

Date: July 12, 2017